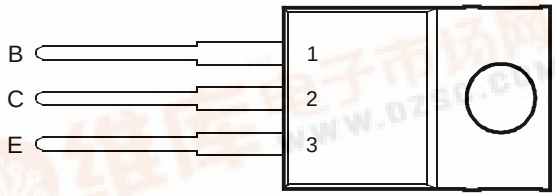
BDW53, BDW53A, BDW53B, BDW53C, BDW53D
NPN SILICON POWER DARLINGTONS

AUGUST 1978 - REVISED MARCH 1997

- **Designed for Complementary Use with BDW54, BDW54A, BDW54B, BDW54C and BDW54D**
- **40 W at 25°C Case Temperature**
- **4 A Continuous Collector Current**
- **Minimum h_{FE} of 750 at 3 V, 1.5 A**

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

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absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage (I_E = 0)	BDW53	V_{CBO}	45	V
	BDW53A		60	
	BDW53B		80	
	BDW53C		100	
	BDW53D		120	
Collector-emitter voltage (I_B = 0) (see Note 1)	BDW53	V_{CEO}	45	V
	BDW53A		60	
	BDW53B		80	
	BDW53C		100	
	BDW53D		120	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	4	A
Continuous base current		I_B	50	mA
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	40	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Unclamped inductive load energy (see Note 4)		$½LI_C^2$	25	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Operating temperature range		T_{stg}	-65 to +150	°C
Operating free-air temperature range		T_A	-65 to +150	°C

NOTES: 1. These values apply when the base-emitter diode is open circuited.
2. Derate linearly to 150°C case temperature at the rate of 0.32 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 5 mA, R_{BE} = 100 Ω, $V_{BE(off)}$ = 0, R_S = 0.1 Ω, V_{CC} = 20 V.

BDW53, BDW53A, BDW53B, BDW53C, BDW53D
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electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS				MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C = 30 mA	I_B = 0	(see Note 5)	BDW53	45			V
					BDW53A	60			
					BDW53B	80			
					BDW53C	100			
					BDW53D	120			
I_{CEO}	Collector-emitter cut-off current	V_{CE} = 30 V	I_B = 0		BDW53			0.5	mA
		V_{CE} = 30 V	I_B = 0		BDW53A			0.5	
		V_{CE} = 40 V	I_B = 0		BDW53B			0.5	
		V_{CE} = 50 V	I_B = 0		BDW53C			0.5	
		V_{CE} = 60 V	I_B = 0		BDW53D			0.5	
I_{CBO}	Collector cut-off current	V_{CB} = 45 V	I_E = 0		BDW53			0.2	mA
		V_{CB} = 60 V	I_E = 0		BDW53A			0.2	
		V_{CB} = 80 V	I_E = 0		BDW53B			0.2	
		V_{CB} = 100 V	I_E = 0		BDW53C			0.2	
		V_{CB} = 120 V	I_E = 0		BDW53D			0.2	
		V_{CB} = 45 V	I_E = 0	T_C = 150°C	BDW53			5	
		V_{CB} = 60 V	I_E = 0	T_C = 150°C	BDW53A			5	
		V_{CB} = 80 V	I_E = 0	T_C = 150°C	BDW53B			5	
		V_{CB} = 100 V	I_E = 0	T_C = 150°C	BDW53C			5	
		V_{CB} = 120 V	I_E = 0	T_C = 150°C	BDW53D			5	
I_{EBO}	Emitter cut-off current	V_{EB} = 5 V	I_C = 0					2	mA
h_{FE}	Forward current transfer ratio	V_{CE} = 3 V	I_C = 1.5 A	(see Notes 5 and 6)		750		20000	
		V_{CE} = 3 V	I_C = 4 A			100			
$V_{BE(on)}$	Base-emitter voltage	V_{CE} = 3 V	I_C = 1.5 A	(see Notes 5 and 6)				2.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_B = 30 mA	I_C = 1.5 A	(see Notes 5 and 6)				2.5	V
		I_B = 40 mA	I_C = 4 A					4	
V_{EC}	Parallel diode forward voltage	I_E = 4 A	I_B = 0					3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, t_p = 300 µs, duty cycle ≤ 2%.
6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			3.125	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on}	Turn-on time	I_C = 2 A	$I_{B(on)}$ = 8 mA	$I_{B(off)}$ = -8 mA		1		µs
t_{off}	Turn-off time	$V_{BE(off)}$ = -5 V	R_L = 15 Ω	t_p = 20 µs, dc ≤ 2%		4.5		µs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT

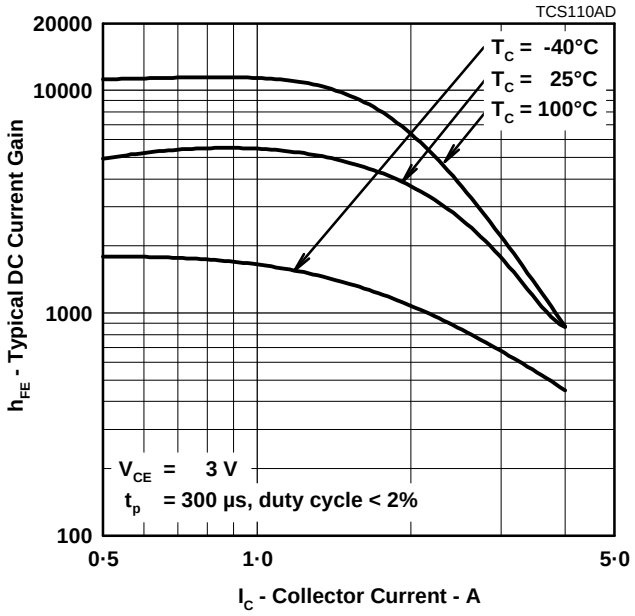

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT

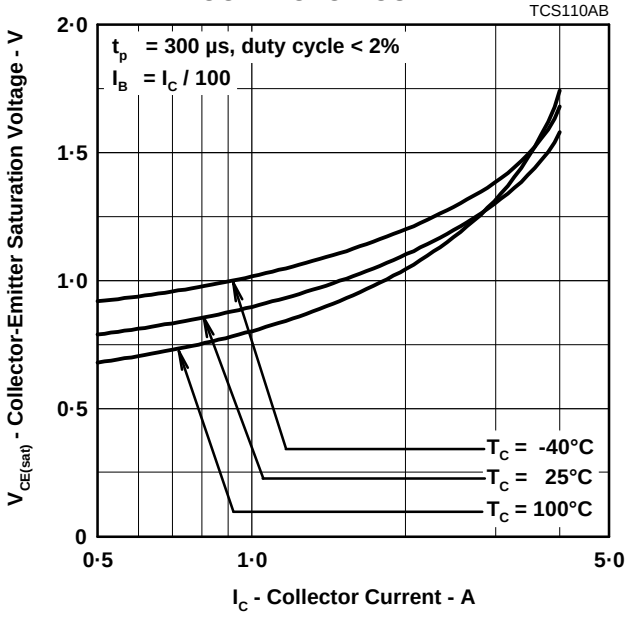

Figure 2.

BASE-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT

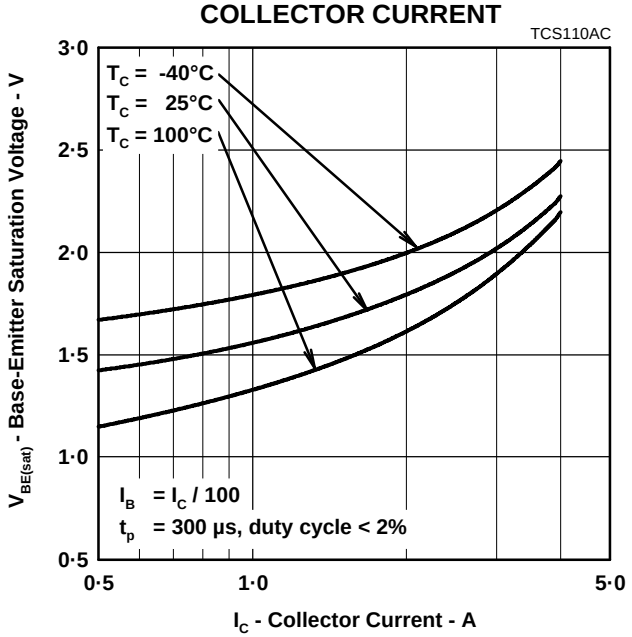

Figure 3.

MAXIMUM SAFE OPERATING REGIONS

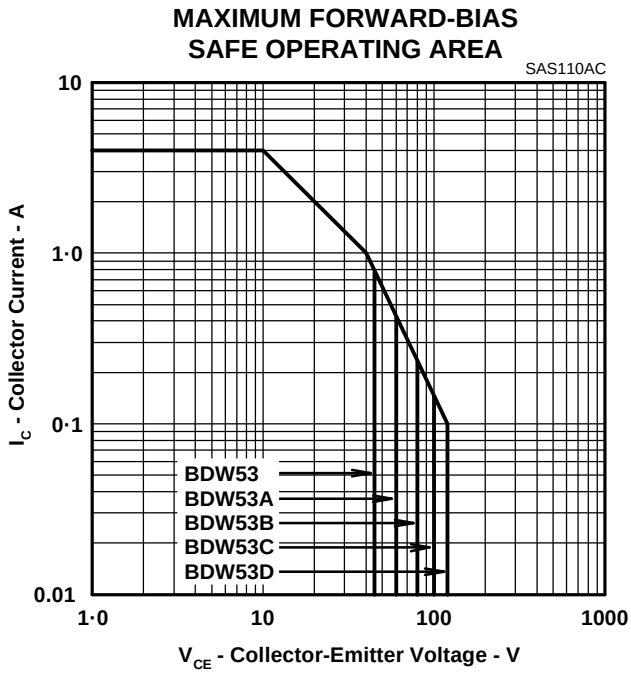

Figure 4.

THERMAL INFORMATION

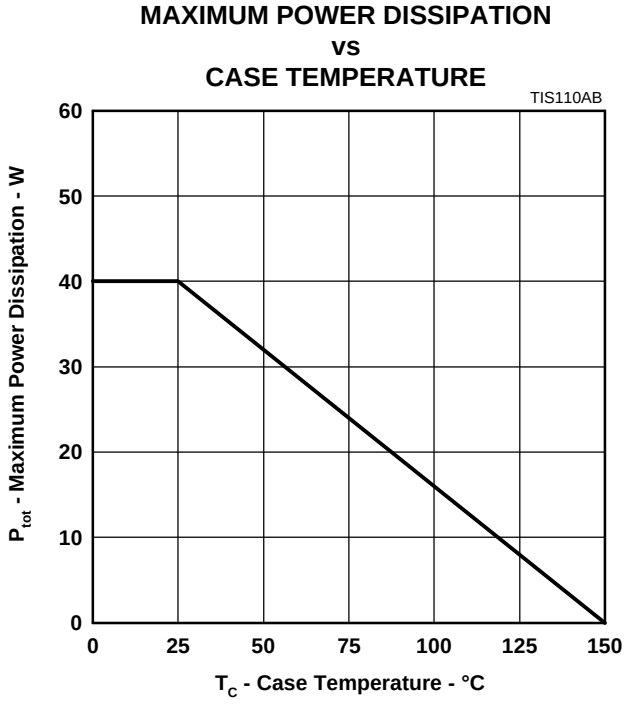

Figure 5.

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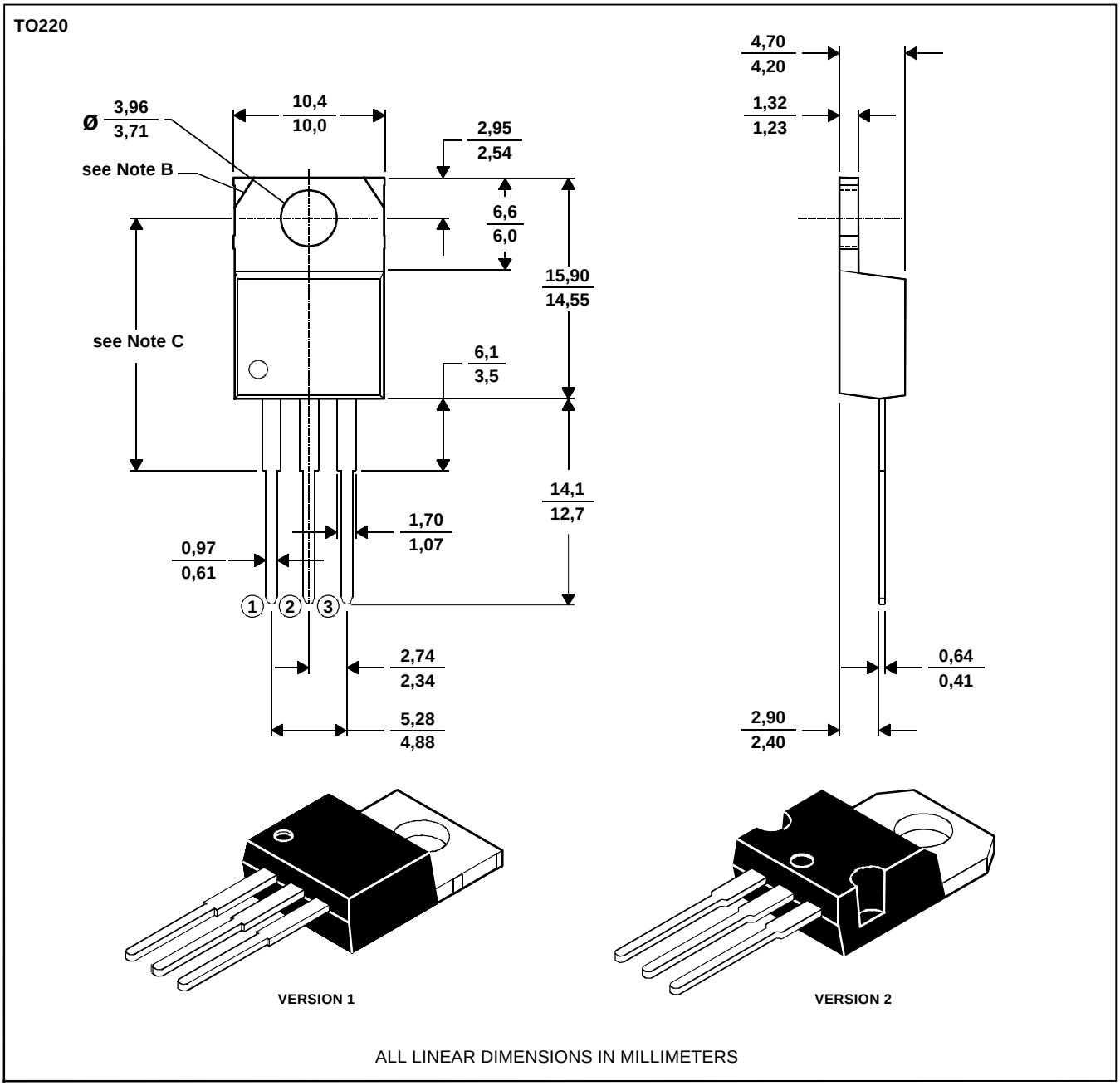
MECHANICAL DATA

TO-220
3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTES: A. The centre pin is in electrical contact with the mounting tab.
B. Mounting tab corner profile according to package version.
C. Typical fixing hole centre stand off height according to package version.
Version 1, 18.0 mm. Version 2, 17.6 mm.

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